- Each Device Drives 32 Lines
- 60-V Output Voltage Swing Capability
- 25-mA Output Source Current Capability
- High-Speed Serially Shifted Data Input
- Latches on All Driver Outputs

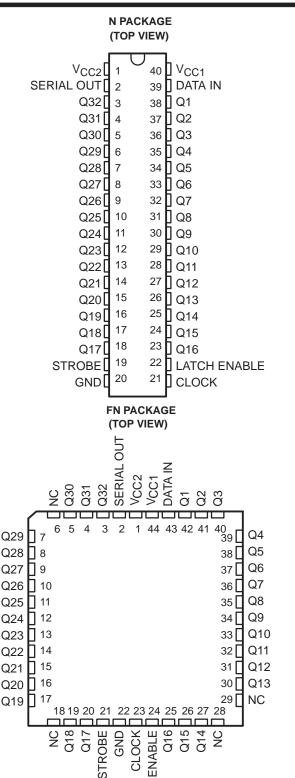
#### description

The SN65518 and SN75518 are monolithic BIDFET<sup>†</sup> integrated circuits designed to drive a dot matrix or segmented vacuum fluorescent display.

Each device consists of a 32-bit shift register, 32 latches, and 32 output AND gates. Serial data is entered into the shift register on the low-to-high transition of CLOCK. While LATCH ENABLE is high, parallel data is transferred to the output buffers through a 32-bit latch. Data present in the latch during the high-to-low transition of LATCH ENABLE is latched. When STROBE is low, all Q outputs are enabled. When STROBE is high, all Q outputs are low.

Serial data output from the shift register may be used to cascade additional devices. This output is not affected by LATCH ENABLE or STROBE.

The SN65518 is characterized for operation from –40°C to 85°C. The SN75518 is characterized for operation from 0°C to 70°C.



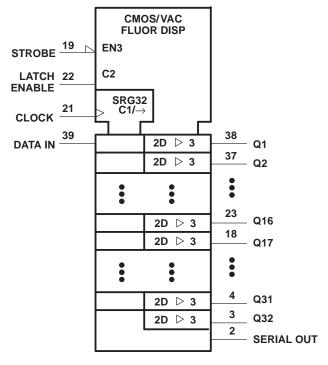
NC - No internal connection

†BIDFET – Bipolar, double-diffused, N-channel and P-channel MOS transistors on same chip. This is a patented process.



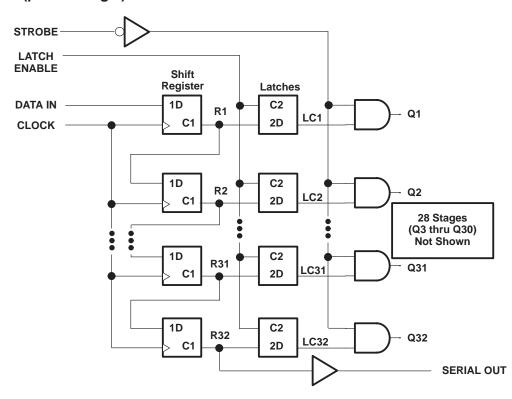
-ATCH

## logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the N package.

## logic diagram (positive logic)





# SN65518, SN75518 VACUUM FLUORESCENT DISPLAY DRIVERS

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#### **FUNCTION TABLE**

	CONTROL INPUTS			SHIFT REGISTERS	LATCHES	OUTPUTS		
FUNCTION	CLOCK	LATCH ENABLE	STROBE	R1 THRU R32	LC1 THRU LC32	SERIAL	Q1 THRU Q32	
Load	↑ No ↑	X X	X X	Load and shift <sup>†</sup> No change	Determined by LATCH ENABLE‡	R32	Determined by STROBE	
Latch	X X	L H	X X	As determined above	Stored data New data	R32	Determined by STROBE	
Strobe	X X	X X	H	As determined above	Determined by LATCH ENABLE‡	R32	All L LC1 thru LC32, respectively	

H = high level, L = low level, X = irrelevant,  $\uparrow = low-to-high-level transition$ .

# typical operating sequence

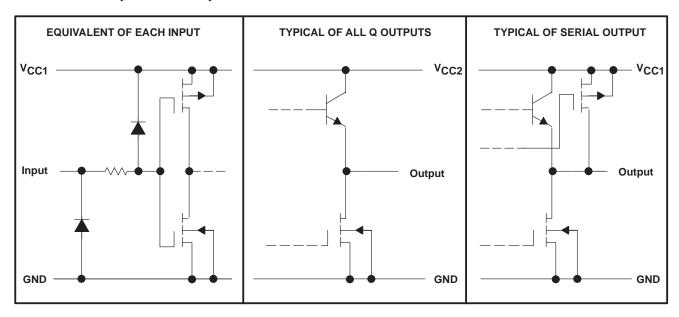
CLOCK		
DATA IN	Valid	Irrelevant
SR Contents	Invalid	Valid
LATCH ENABLE		
Latch Contents	Previously Stored Data	New Data Valid
STROBE		
Q Outputs		Valid

<sup>†</sup>R32 and the serial output take on the state of R31, R31 takes on the state of R30, ... R2 takes on the state of R1, and R1 takes on the state of the data input.

<sup>‡</sup> New data enter the latches while LATCH ENABLE is high. These data are stored while LATCH ENABLE is low.

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## schematic of inputs and outputs



## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V <sub>CC1</sub> (see Note 1)	15 V
Supply voltage, V <sub>CC2</sub>	70 V
Input voltage, V <sub>I</sub>	V <sub>CC1</sub>
Continuous total power dissipation	
Operating free-air temperature range, T <sub>A</sub> : SN65518	–40°C to 85°C
SN75518	0°C to 70°C
Storage temperature range, T <sub>stq</sub>	65°C to 150°C
Case temperature for 10 seconds: FN package	
Lead temperature 1,6 mm (1/16 inch) from case for 10	

NOTE 1: Voltage values are with respect to network ground terminal.

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING	
FN	1700 mW	13.6 mW/°C	1088 mW	884 mW	
N	1250 mW	10.0 mW/°C	800 mW	650 mW	

# recommended operating conditions, $T_A = 25$ °C (unless otherwise noted)

		MIN	MAX	UNIT	
Supply voltage, V <sub>CC1</sub>	4.5	15	V		
Supply voltage, V <sub>CC2</sub>	0	60	V		
High-level input voltage, VIH (see Figure 1)	V <sub>CC1</sub> = 4.5 V	3.5		V	
Thigh level input voltage, VIH (see Figure 1)	V <sub>CC1</sub> = 15 V	12		V	
Low-level input voltage, V <sub>IL</sub> (see Figure 1)		-0.3	0.8	V	
High-level output current, IOH	High-level output current, IOH				
Low-level output current, IOL	Low-level output current, IOL				
Clock frequency, f <sub>clock</sub> (see Figure 2)	V <sub>CC1</sub> = 10 V to 15 V	0	5	MHz	
	V <sub>CC1</sub> = 4.5 V	0	1		
Bulgo duration CLOCK high to court	V <sub>CC1</sub> = 10 V to 15 V	100		ns	
Pulse duration, CLOCK high, t <sub>W</sub> (CKH)	V <sub>CC1</sub> = 4.5 V	500			
Pulse duration, CLOCK low, tw(CKL)	V <sub>CC1</sub> = 10 V to 15 V	100		ns	
Fulse duration, GLOCK low, tw(CKL)	V <sub>CC1</sub> = 4.5 V	500			
Setup time, DATA IN before CLOCK↑, t <sub>SU</sub>	V <sub>CC1</sub> = 10 V to 15 V	75		ns	
Setup time, DATA IN Delote CLOCKT, ISU	V <sub>CC1</sub> = 4.5 V	150			
Hold time, DATA IN after CLOCK↑, th	V <sub>CC1</sub> = 10 V to 15 V	75		nc	
	V <sub>CC1</sub> = 4.5 V	150		ns	
Operating free-air temperature, T <sub>A</sub>	SN65518	-40	85	°C	
Operating free-all temperature, 14	SN75518	0	70		

# electrical characteristics over recommended ranges of operating free-air temperature and $V_{CC1}$ , $V_{CC2}$ = 60 V (unless otherwise noted)

	PARAMETER		TEST	CONDITIONS	MIN	TYP <sup>†</sup>	MAX	UNIT
VIK	Input clamp voltage		I <sub>I</sub> = -12 mA				-1.5	V
V	High-level output voltage	Q outputs	I <sub>OH</sub> = -25 mA		57.5	58		V
VOH	riigii-ievei output voitage	SERIAL OUT	$V_{CC1} = 5 V$	I <sub>OH</sub> = – 20 μA	4.5	4.9	5	
Vai	Low-level output voltage	Q outputs	I <sub>OL</sub> = 1 mA				5	V
V <sub>OL</sub> Low-level output voltage		SERIAL OUT	I <sub>OL</sub> = 20 μA			0.06	0.8	V
lіН	High-level input current		V <sub>CC1</sub> = 15 V,	V <sub>I</sub> = 15 V		0.1	1	μΑ
I <sub>I</sub> L	Low-level input current		V <sub>CC1</sub> = 15 V,	V <sub>I</sub> = 0 V		-0.1	-1	μΑ
I <sub>CC1</sub> Supply current			V <sub>CC1</sub> = 4.5 V			1.8	4	mA
			V <sub>CC1</sub> = 15 V			2	5	
		SN65518	Outputs high,	$T_A = -40^{\circ}C$			12	
ICC2	Supply current	SN65518,	Outputs high,	$T_A = 0^{\circ}C$ to MAX		7	10	mA
		SN75518	Outputs low			0.01	0.5	

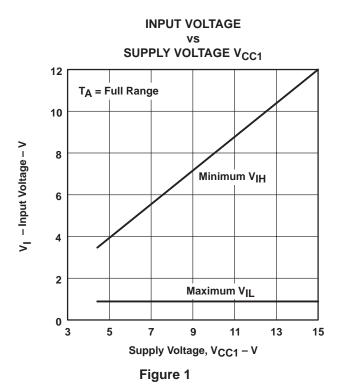
<sup>&</sup>lt;sup>†</sup> All typical values are at  $T_A = 25$ °C.

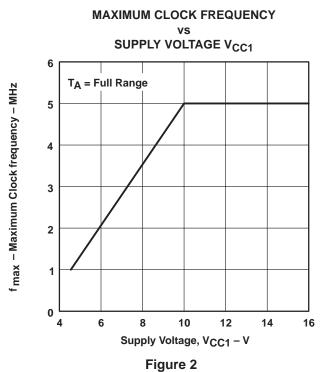
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# switching characteristics, $V_{CC2}$ = 60 V, $C_L$ = 50 pF, $T_A$ = 25°C (unless otherwise noted)

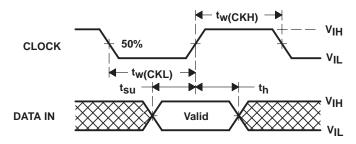
PARAMETER			TEST CONDITIONS		MIN MAX	UNIT
t <sub>d</sub> Delay time, CLOCK to DATA OUT			V <sub>CC1</sub> = 4.5 V	C <sub>L</sub> = 15 pF,	600	ns
<sup>t</sup> d	Delay time, CLOCK to DATA OUT		V <sub>CC1</sub> = 15 V	See Figure 4	150	115
		From LATCH ENABLE	V221 - 45 V	See Figure 5	1.5	μs
<b> </b>	Delay time high to love level O cutout	From STROBE	V <sub>CC1</sub> = 4.5 V	See Figure 6	1	
tDHL	Delay time, high-to-low-level Q output	From LATCH ENABLE	V 15 V	See Figure 5	0.5	
		From STROBE	V <sub>CC1</sub> = 15 V	See Figure 6	0.5	
	Delay time, low-to-high-level Q output	From LATCH ENABLE	V <sub>CC1</sub> = 4.5 V	See Figure 5	1.5	μs
<b>.</b>		From STROBE		See Figure 6	1	
tDLH		From LATCH ENABLE	V <sub>CC1</sub> = 15 V	See Figure 5	0.25	
		From STROBE		See Figure 6	0.25	
<b>.</b>	Transition times bink to law law lovel O codes		V <sub>CC1</sub> = 4.5 V	Caa Figura C	3	
tTHL Transition time, high-to-low-level Q outpu		II.	V <sub>CC1</sub> = 15 V	See Figure 6	1.5	μs
			V <sub>CC1</sub> = 4.5 V	0 5 0	2.5	μs
tTLH	Transition time, low-to-high-level Q output	V <sub>CC1</sub> = 15 V	See Figure 6	0.75		

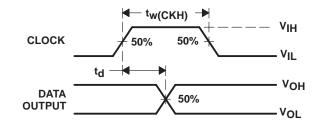
#### RECOMMENDED OPERATING CONDITIONS





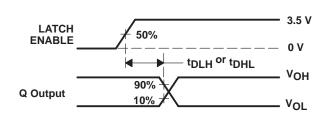
#### PARAMETER MEASUREMENT INFORMATION<sup>†</sup>





**Figure 3. Input Timing Waveforms** 

Figure 4. Data Output Switching Times



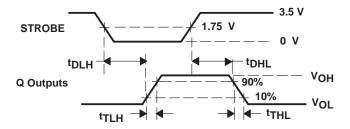


Figure 5. Q Output Switching Times

Figure 6. Switching Time Voltage Waveforms

† For testing purposes, all input pulses have maximum rise and fall times of 30 ns.

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